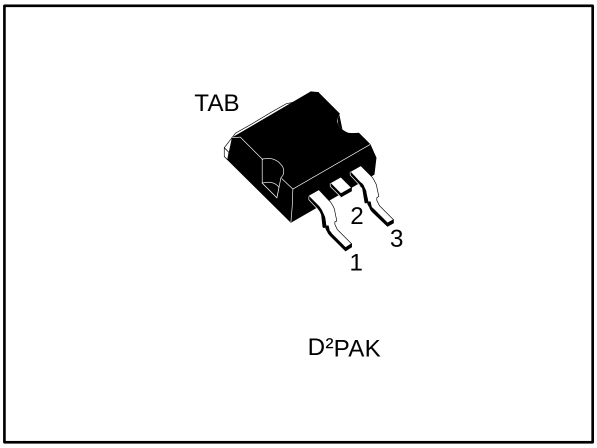
STB10LN80K5

N-channel 800 V, 0.55 Ω typ., 8 A MDmesh™ K5 Power MOSFET in a D²PAK package

Datasheet - production data



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STB10LN80K5	800 V	0.63 Ω	8 A

- Industry's lowest $R_{DS(on)}$ x area
- Industry's best figure of merit (FoM)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Figure 1: Internal schematic diagram

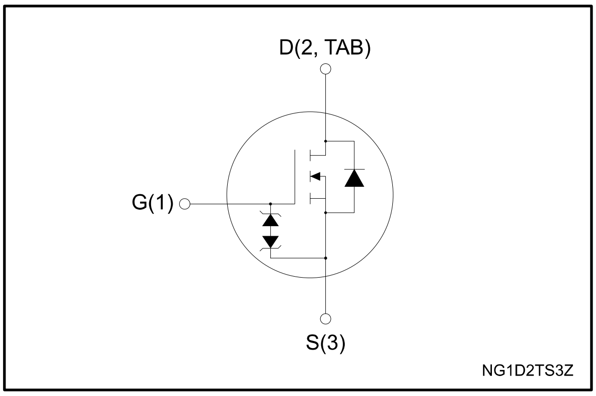


Table 1: Device summary

Order code	Marking	Package	Packing
STB10LN80K5	10LN80K5	D^2PAK	Tape and reel

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at T_C = 25 °C	8	A
I_D	Drain current (continuous) at T_C = 100 °C	5	A
I_D(1)	Drain current (pulsed)	32	A
P_{TOT}	Total dissipation at T_C = 25 °C	110	W
dv/dt (2)	Peak diode recovery voltage slope	4.5	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	
T_j	Operating junction temperature range	- 55 to 150	°C
T_{stg}	Storage temperature range		

Notes:

(1)Pulse width limited by safe operating area.

(2)$I_{SD} \leq 8$ A, di/dt ≤ 100 A/µs; V_{DS} peak < $V_{(BR)DSS}$

(3)$V_{DS} \leq 640$ V

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.14	°C/W
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb	35	°C/W

Notes:

(1)When mounted on FR-4 board of 1 inch² , 2 oz Cu

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	2.7	A
E_{AS}	Single pulse avalanche energy (starting Tj = 25 ° C, $I_D = I_{AR}$, V_{DD} = 50 V)	240	mJ

2 Electrical characteristics

T_C = 25 ° C unless otherwise specified

Table 5: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	800			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 800 V			1	µA
		V_{GS} = 0 V, V_{DS} = 800 V T_C = 125 °C			50	µA
I_{GSS}	Gate body leakage current	V_{DS} = 0 V, V_{GS} = ± 20 V			± 10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 4 A		0.55	0.63	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	427	-	pF
C_{oss}	Output capacitance		-	43	-	pF
C_{rss}	Reverse transfer capacitance		-	0.25	-	pF
$C_{o(tr)}$ *(1)*	Equivalent capacitance time related	V_{DS} = 0 to 640 V, V_{GS} = 0 V	-	72	-	pF
$C_{o(er)}$ *(2)*	Equivalent capacitance energy related			27	-	pF
R_g	Intrinsic gate resistance	f = 1 MHz , I_D= 0 A	-	7	-	Ω
Q_g	Total gate charge	V_{DD} = 640 V, I_D = 8 A V_{GS}= 10 V See *Figure 16: "Test circuit for gate charge behavior"*	-	15	-	nC
Q_{gs}	Gate-source charge		-	4.2	-	nC
Q_{gd}	Gate-drain charge		-	9	-	nC

Notes:

(1)Time related is defined as a constant equivalent capacitance giving the same charging time as Coss when V_{DS} increases from 0 to 80% V_{DSS}

(2)Energy related is defined as a constant equivalent capacitance giving the same stored energy as Coss when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}= 400 V, I_D = 4 A, R_G = 4.7 Ω V_{GS} = 10 V See *Figure 15: "Test circuit for resistive load switching times"* and *Figure 20: "Switching time waveform"*	-	11.8	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	28	-	ns
t_f	Fall time		-	13	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		8	A
I_{SDM}(1)	Source-drain current (pulsed)		-		32	A
V_{SD}(2)	Forward on voltage	I_{SD} = 8 A, V_{GS} = 0 V	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 8 A, di/dt = 100 A/µs, V_{DD} = 60 V See *Figure 17: "Test circuit for inductive load switching and diode recovery times"*	-	350		ns
Q_{rr}	Reverse recovery charge		-	3.9		µC
I_{RRM}	Reverse recovery current		-	22.5		A
t_{rr}	Reverse recovery time	I_{SD} = 8 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C See *Figure 17: "Test circuit for inductive load switching and diode recovery times"*	-	505		ns
Q_{rr}	Reverse recovery charge		-	5		µC
I_{RRM}	Reverse recovery current		-	20		A

Notes:

(1)Pulse width limited by safe operating area

(2)Pulsed: pulse duration = 300 µ s, duty cycle 1.5%

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS}= ± 1mA, I_D= 0 A	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection,thus eliminating the need for additional external componentry.

2.2 Electrical characteristics (curves)

Figure 2: Safe operating area

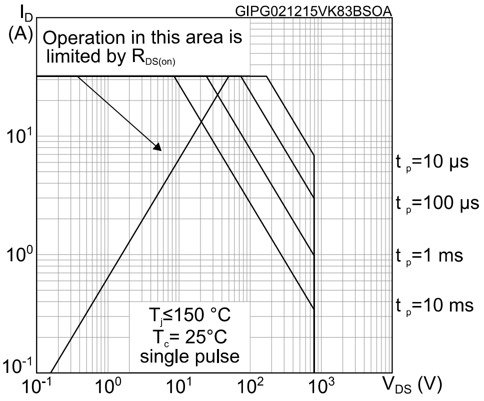


Figure 3: Thermal impedance

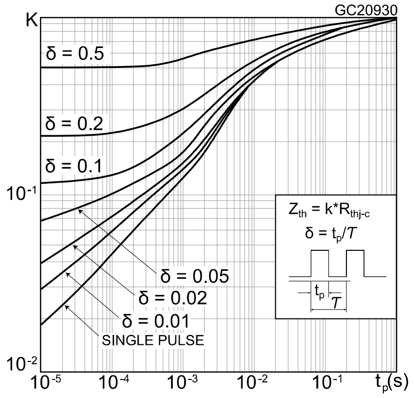


Figure 4: Output characteristics

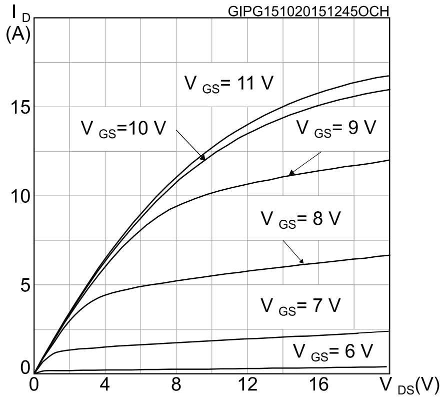


Figure 5: Transfer characteristics

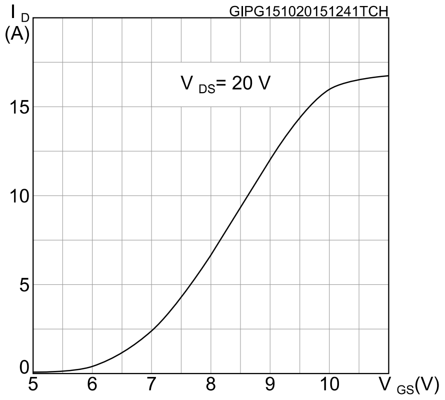


Figure 6: Gate charge vs gate-source voltage

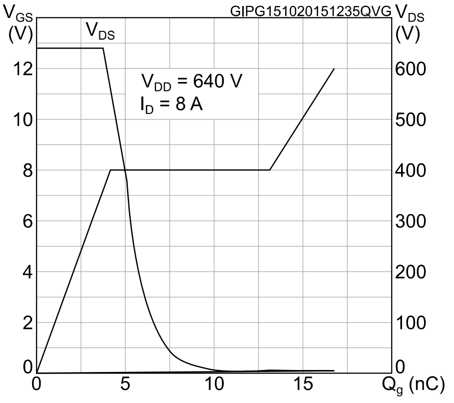


Figure 7: Static drain-source on-resistance

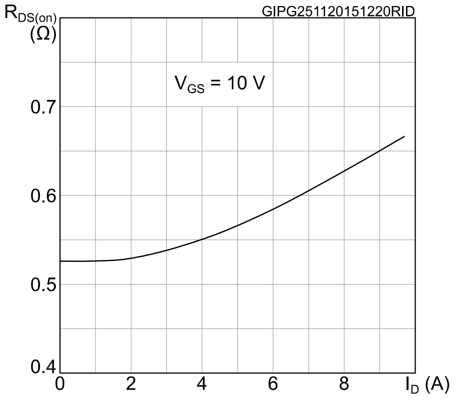


Figure 8: Capacitance variations

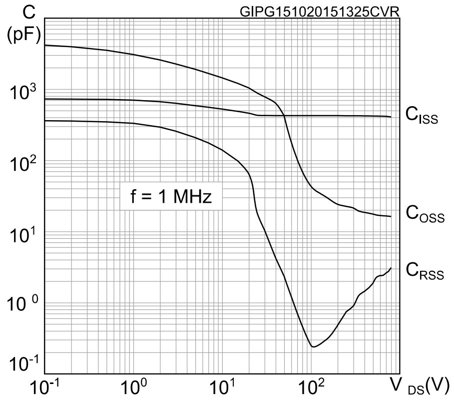


Figure 9: Normalized gate threshold voltage vs temperature

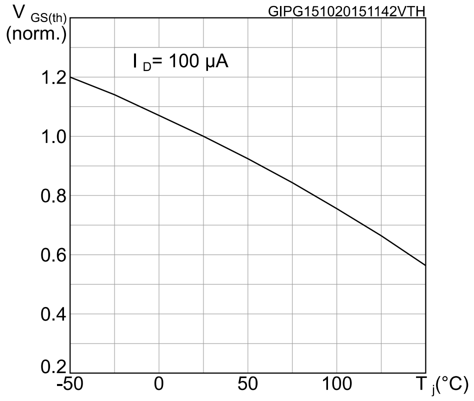


Figure 10: Normalized on-resistance vs temperature

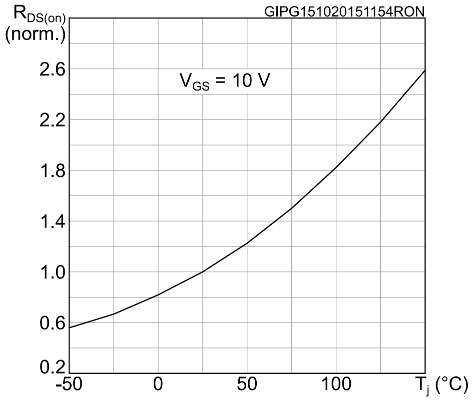


Figure 11: Normalized $V_{(BR)DSS}$ vs temperature

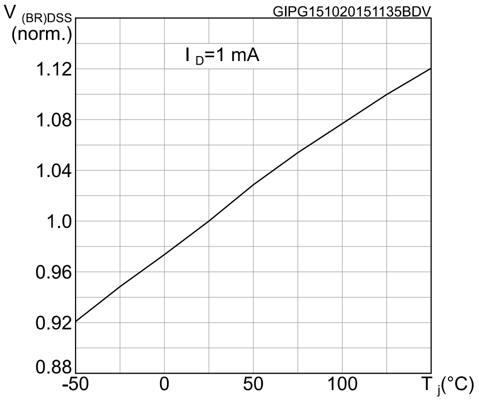


Figure 12: Output capacitance stored energy

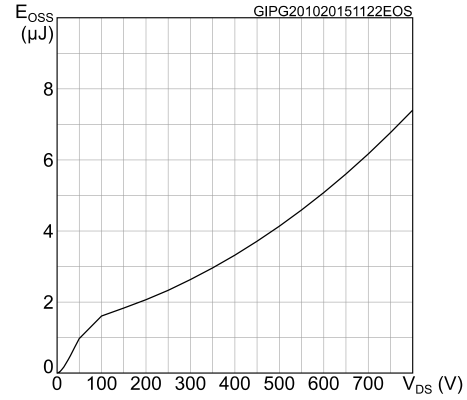


Figure 13: Source-drain diode forward characteristics

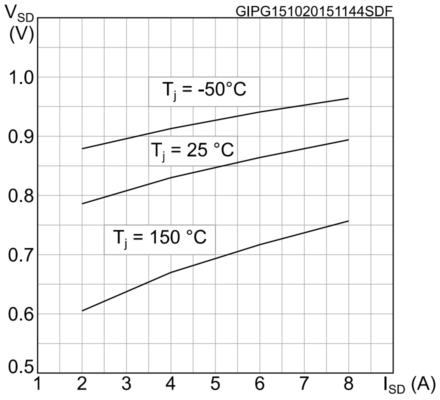
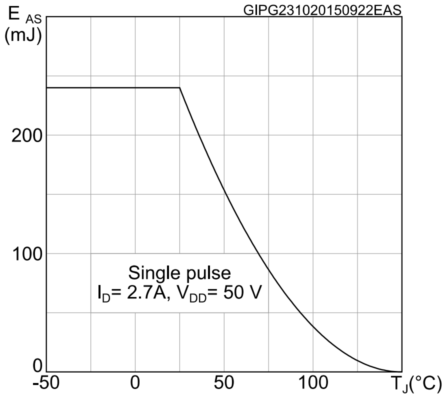


Figure 14: Maximum avalanche energy vs starting T_J



3 Test circuits

Figure 15: Test circuit for resistive load switching times

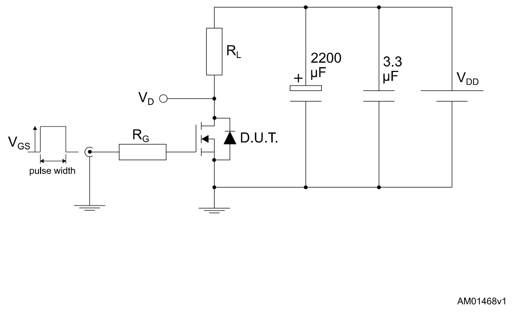


Figure 16: Test circuit for gate charge behavior

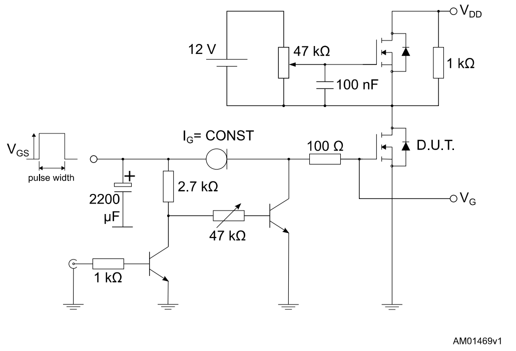


Figure 17: Test circuit for inductive load switching and diode recovery times

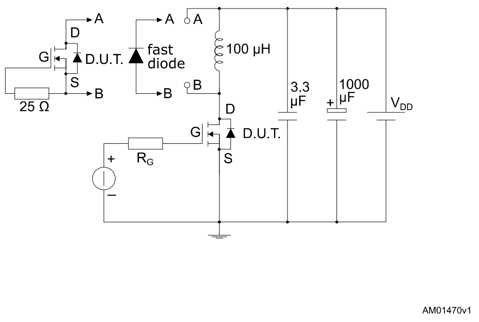


Figure 18: Unclamped inductive load test circuit

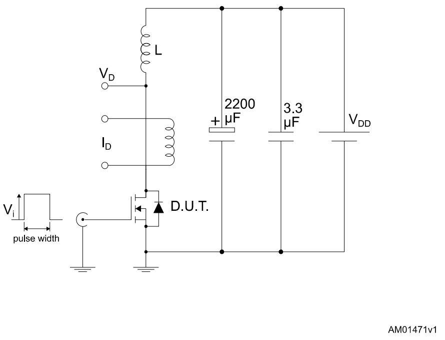


Figure 19: Unclamped inductive waveform

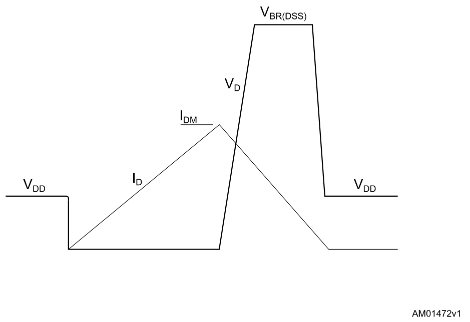
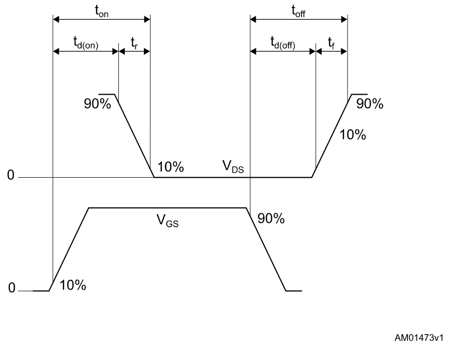


Figure 20: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 D^{2}PAK package information

Figure 21: D²PAK (TO-263) type A package outline

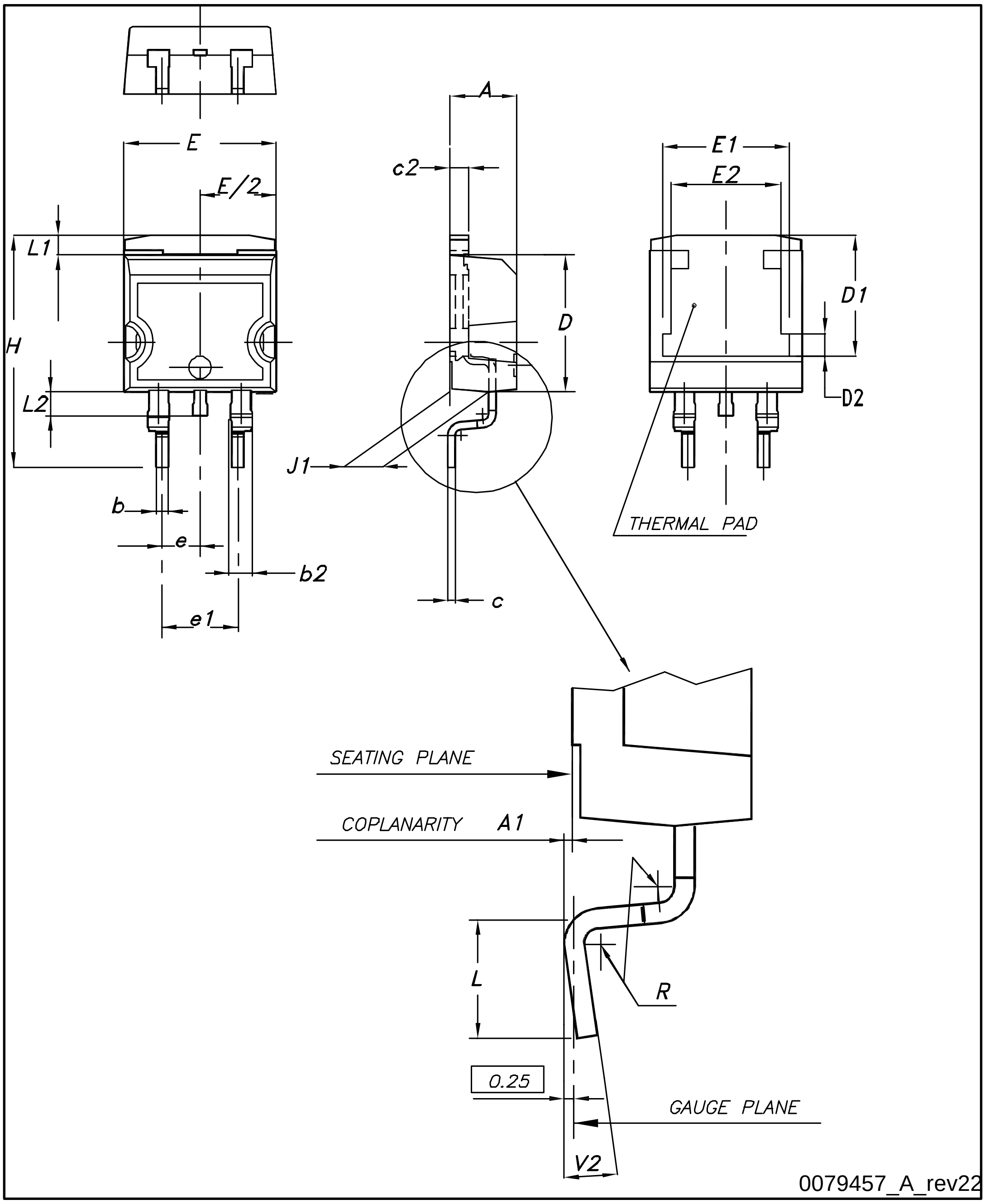
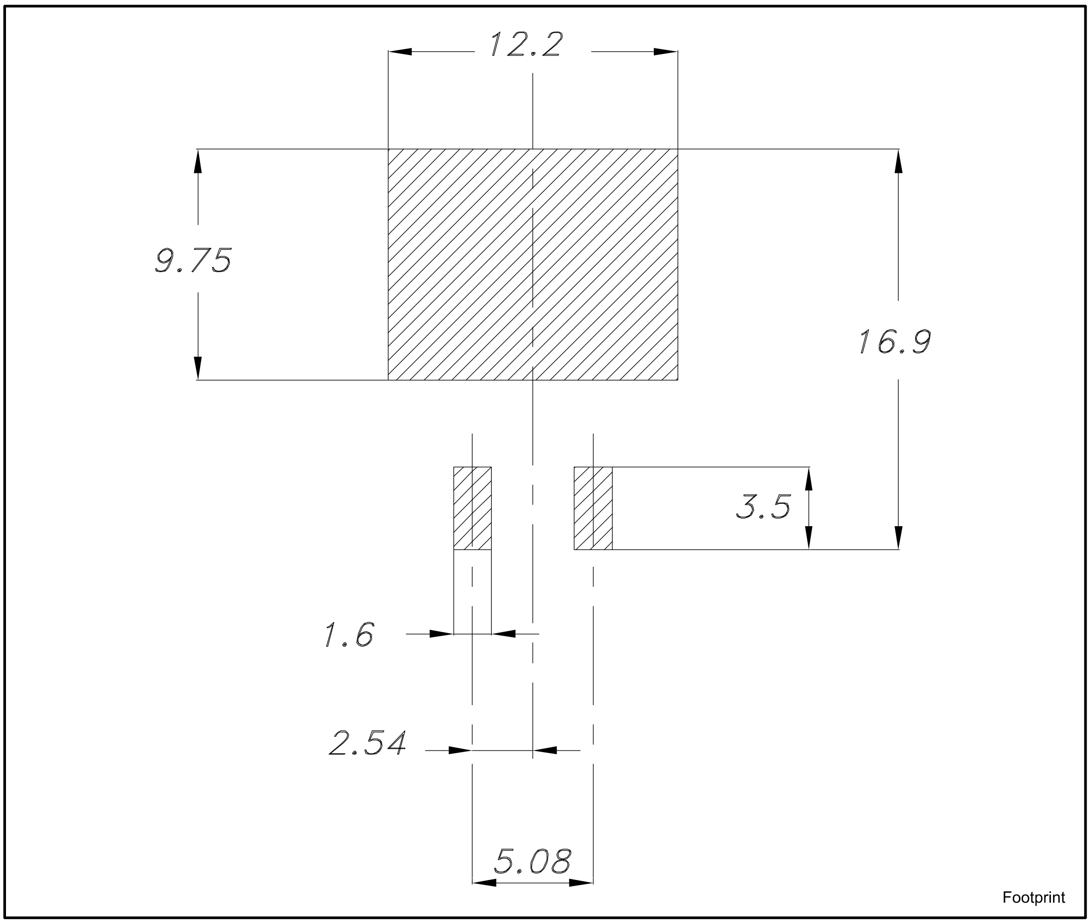


Table 10: D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22: D²PAK (TO-263) recommended footprint (dimensions are in mm)



4.2 Packing information

Figure 23: Tape outline

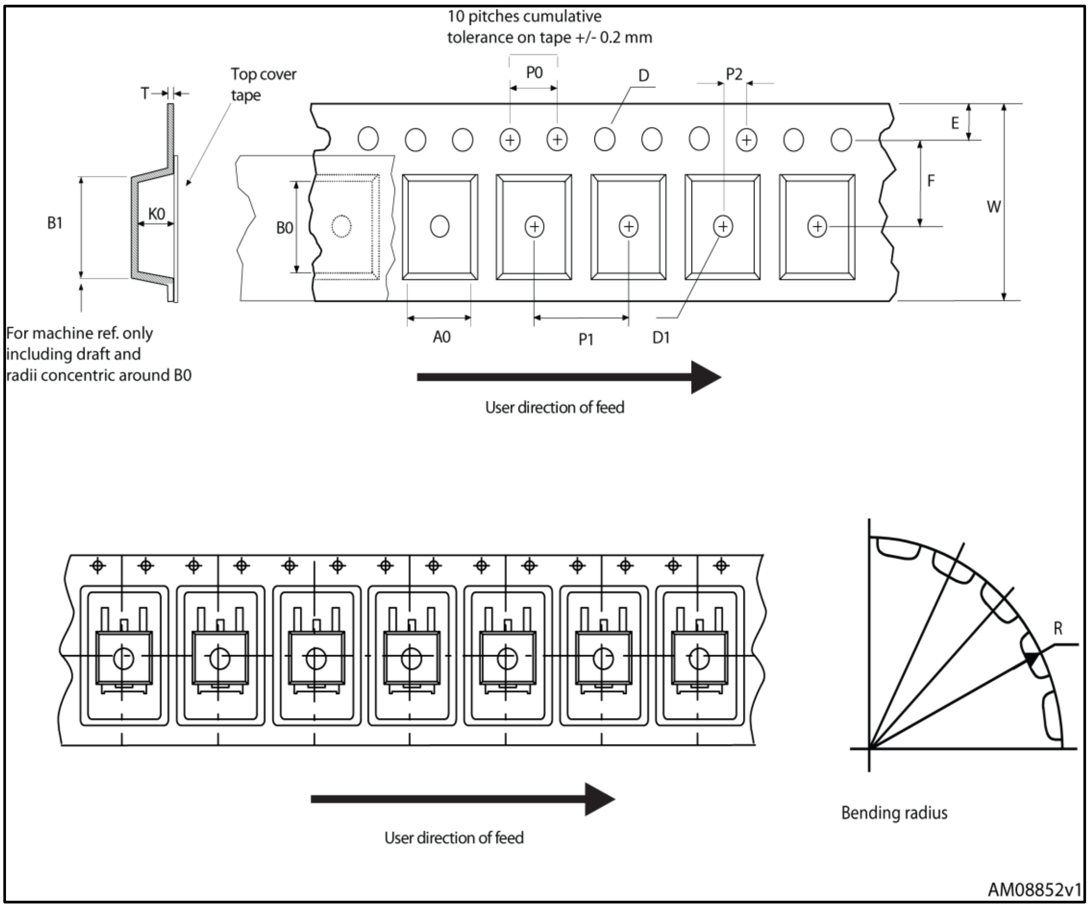


Figure 24: Reel outline

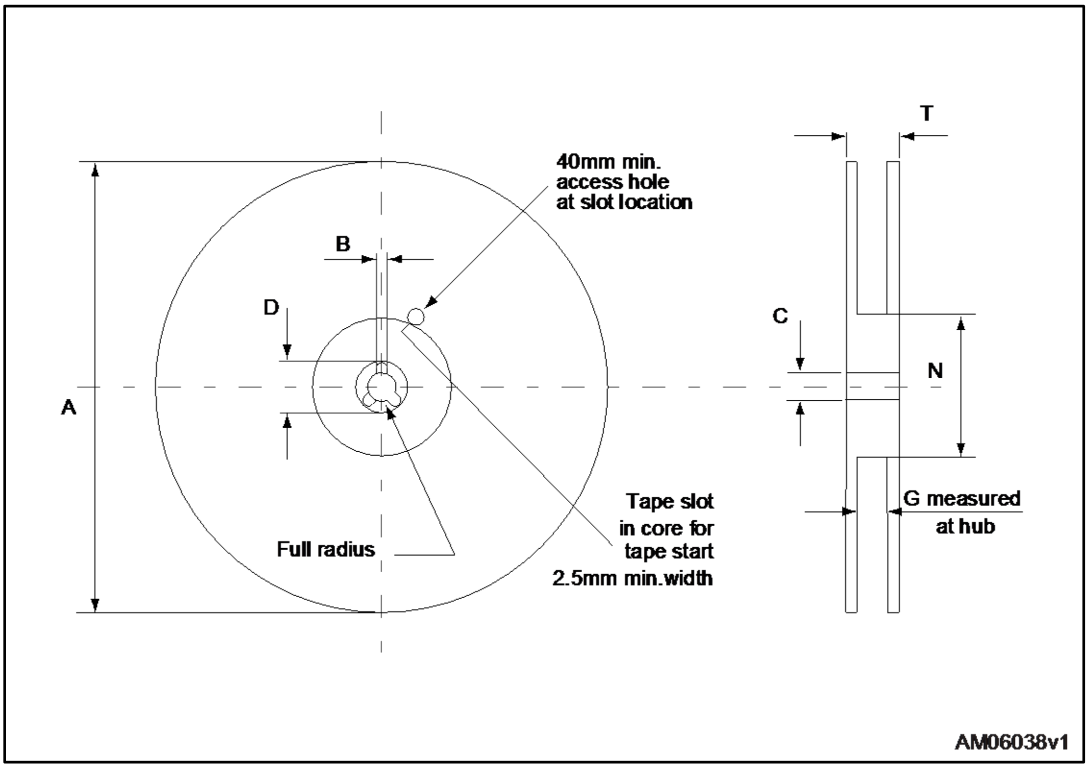


Table 11: D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Revision history

Table 12: Document revision history

Date	Revision	Changes
04-May-2015	1	First release.
08-Feb-2016	2	Modified: *Table 2: "Absolute maximum ratings"*, *Table 3: "Thermal data"*, *Table 4: "Avalanche characteristics"*, *Table 5: "On/off-state"*, *Table 7: "Switching times"* and *Table 8: "Source-drain diode"* Added: *Section 3.1: "Electrical characteristics (curves)"* Datasheet promoted from preliminary data to production data Minor text changes

IMPORTANT NOTICE – PLEASE READ CAREFULLY